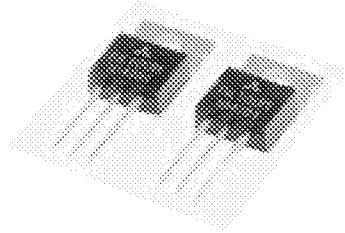


FK10UM-10

HIGH-SPEED SWITCHING USE

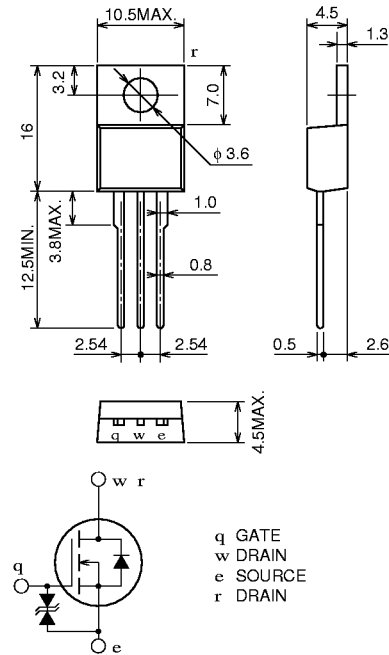
FK10UM-10



- ▾ V_{DSS} 500V
- ▾ r_{DS (ON)} (MAX) 1.13Ω
- ▾ I_D 10A
- ▾ Integrated Fast Recovery Diode (MAX.) 150ns

OUTLINE DRAWING

Dimensions in mm



TO-220

APPLICATION

Servo motor drive, Robot, UPS, Inverter Fluorescent lamp, etc.

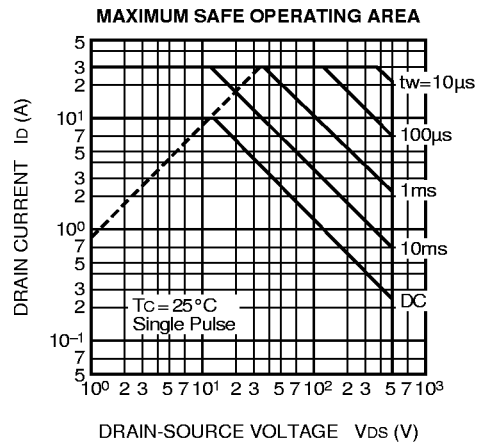
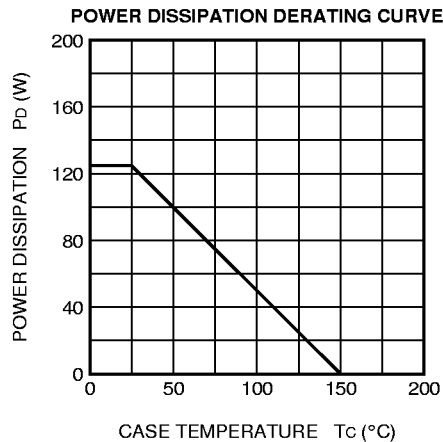
MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	500	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±30	V
I _D	Drain current		10	A
I _{DM}	Drain current (Pulsed)		30	A
I _S	Source current		10	A
I _{SM}	Source current (Pulsed)		30	A
P _D	Maximum power dissipation		125	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	2.0	g

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{(BR) DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0 V	500	—	—	V
V _{(BR) GSS}	Gate-source breakdown voltage	I _G = ±100 μA, V _{DS} = 0 V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25 V, V _{DS} = 0 V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 500 V, V _{GS} = 0 V	—	—	1	mA
V _{GS(th)}	Gate-source threshold voltage	I _D = 1 mA, V _{DS} = 10 V	2	3	4	V
r _{DS(ON)}	Drain-source on-state resistance	I _D = 5 A, V _{GS} = 10 V	—	0.88	1.13	Ω
V _{DS(ON)}	Drain-source on-state voltage	I _D = 5 A, V _{GS} = 10 V	—	4.40	5.65	V
y _{fs}	Forward transfer admittance	I _D = 5 A, V _{DS} = 10 V	3.3	5.5	—	S
C _{iss}	Input capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	—	1100	—	pF
C _{oss}	Output capacitance		—	130	—	pF
C _{rss}	Reverse transfer capacitance		—	20	—	pF
t _{d(on)}	Turn-on delay time	V _{DD} = 200 V, I _D = 5 A, V _{GS} = 10 V, R _{GEN} = R _{GS} = 50 Ω	—	20	—	ns
t _r	Rise time		—	30	—	ns
t _{d(off)}	Turn-off delay time		—	95	—	ns
t _f	Fall time		—	35	—	ns
V _{SD}	Source-drain voltage	I _S = 5 A, V _{GS} = 0 V	—	1.5	2.0	V
R _{th(ch-c)}	Thermal resistance	Channel to case	—	—	1.0	°C/W
t _{rr}	Reverse recovery time	I _S = 10 A, di/dt = -100 A/μs	—	—	150	ns

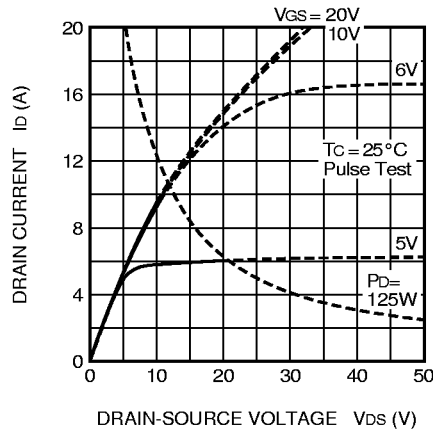
PERFORMANCE CURVES



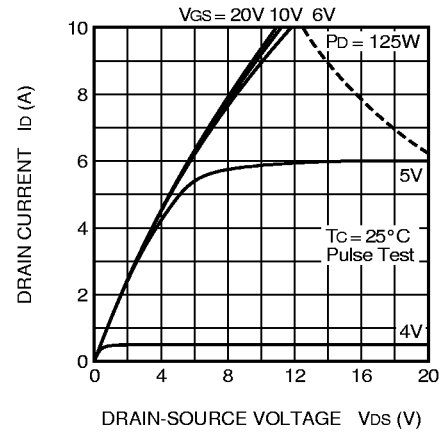
FK10UM-10

HIGH-SPEED SWITCHING USE

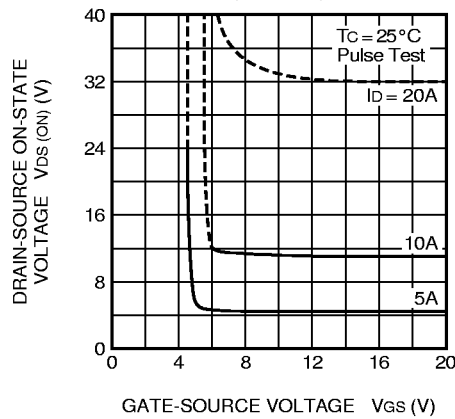
OUTPUT CHARACTERISTICS
(TYPICAL)



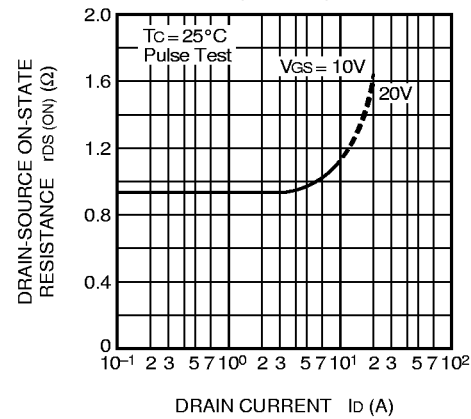
OUTPUT CHARACTERISTICS
(TYPICAL)



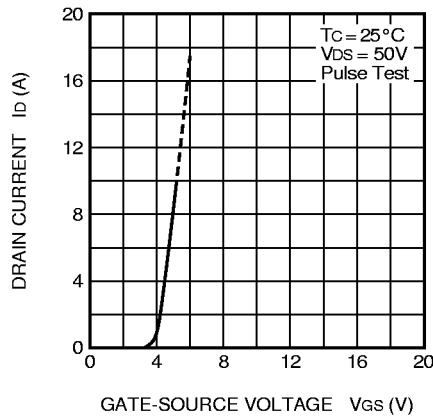
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



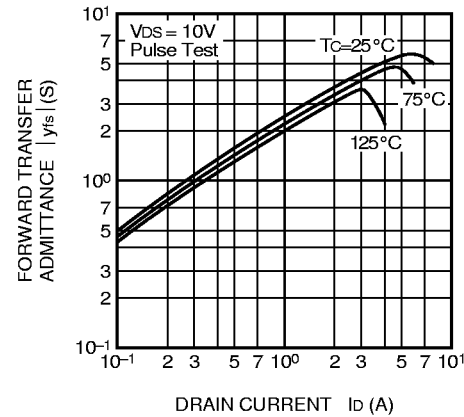
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



TRANSFER CHARACTERISTICS
(TYPICAL)

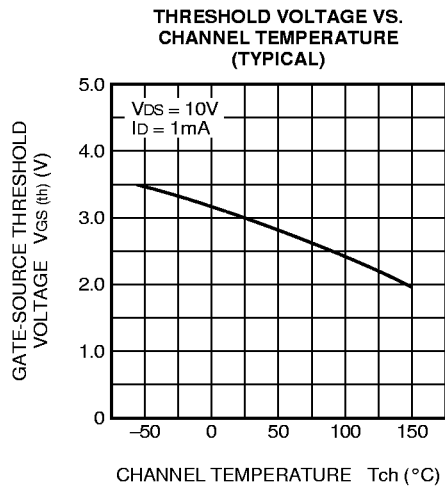
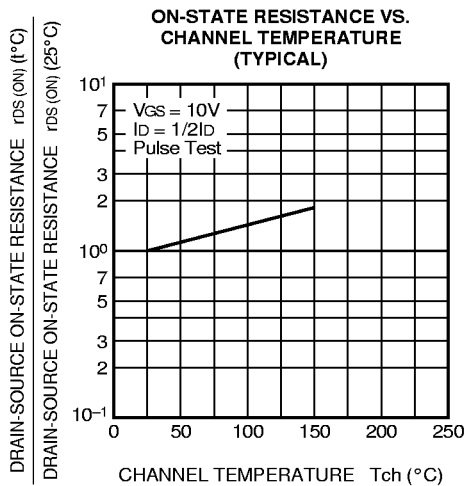
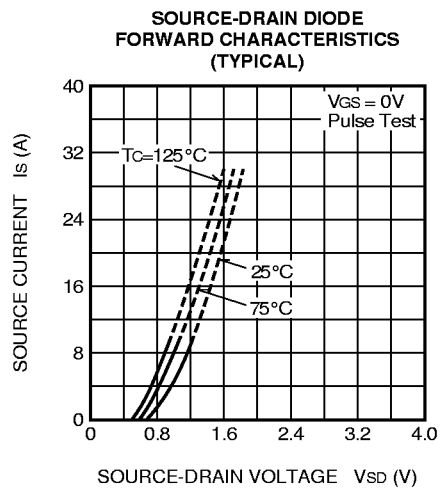
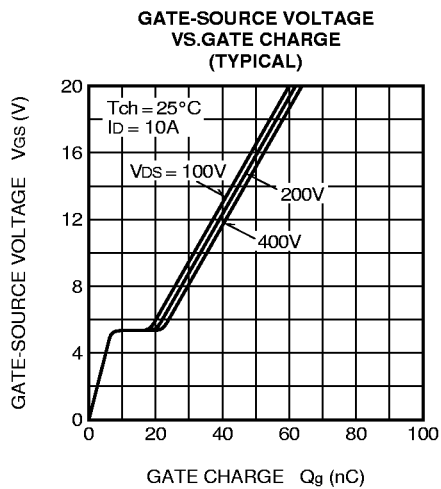
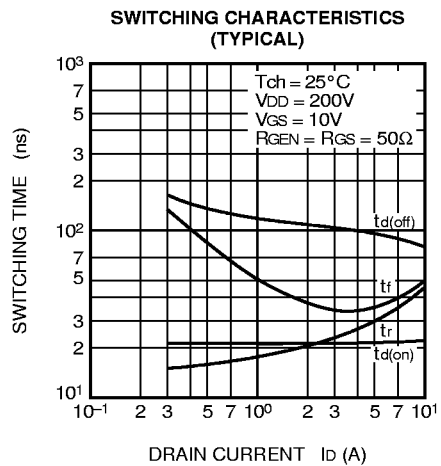
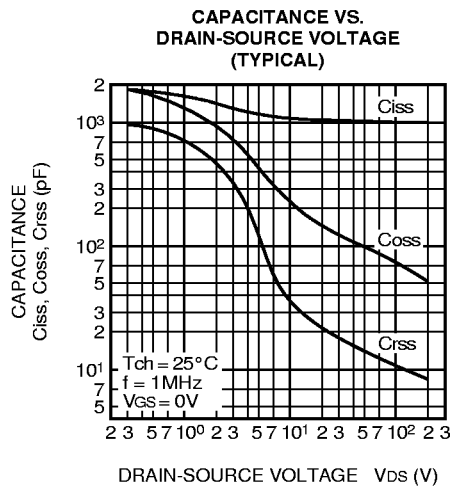


FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)



FK10UM-10

HIGH-SPEED SWITCHING USE



FK10UM-10

HIGH-SPEED SWITCHING USE

